



3DD104

NPN Silicon Low Frequency High Power Transistor



Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications					Test Condition
			A	B	C	D	E	
Collector-Emitter Voltage	V_{CEO}	V	200	300	400	600	800	
Emitter-Base Voltage	V_{EBO}	V	4			8		
Max. Collector Current	I_{CM}	A	3					
Max. Collector Dissipation	P_{CM}	W	50					$T_c:75^\circ\text{C}$
Junction Temperature	T_{jm}	$^\circ\text{C}$	175					
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175					
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:1.0					$V_{CE}=100\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:2		Max.:4			$I_c=3\text{A}, I_B=1\text{A}$
DC Current Gain	h_{FE}		Min.:10					$V_{CE}=10\text{V}, I_c=1.5\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	A	B	C	D	E	$I_c=5\text{mA}$
			200	300	400	600	800	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	4			8		$I_E=5\text{mA}$

Outline and Dimensions: